

ABSTRACT

CHEMICAL MECHANICAL POLISHING LIQUID AND POLISHING METHOD

The present application provides a chemical mechanical polishing liquid, comprising abrasive particles, polyacrylic acid, potassium carbonate, alkyl quaternary ammonium salt, polymerization inhibitor, water and a pH regulator. The present application also provides a polishing method. The introduction of polyacrylic acid and potassium carbonate in the chemical mechanical polishing liquid provided in the present application significantly improves the removal rate of surface materials of silicon dioxide wafers, and the polished silicon dioxide wafers have good surface roughness. Furthermore, using alkyl quaternary ammonium salt as charge balancer and polymerization inhibitor in combination can still keep the concentrated polishing liquid stable under high concentration conditions.

(NO FIG.)